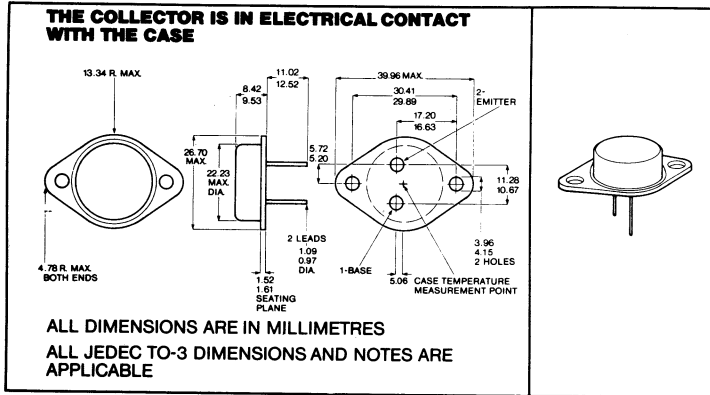


TYPES 2N6326, 2N6327, 2N6328 N-P-N SILICON POWER TRANSISTORS

FOR POWER-AMPLIFIER AND HIGH-SPEED-SWITCHING APPLICATIONS
DESIGNED FOR COMPLEMENTARY USE WITH 2N6329, 2N6330, 2N6331

- 200 W at 25°C Case Temperature
- 30-A Rated Collector Current
- 200-mJ Reverse Energy Rating
- High SOA Capability, 20 V and 10 A

*mechanical data



*absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	2N6326	2N6327	2N6328
Collector-Base Voltage	60 V	80 V	100 V
Collector-Emitter Voltage (See Note 1)	60 V	80 V	100 V
Emitter-Base Voltage	5 V	5 V	5 V -
Continuous Collector Current	← 30 A →		
Peak Collector Current (See Note 2)	← 40 A →		
Continuous Base Current	← 10 A →		
Safe Operating Areas at (or below) 25°C Case Temperature	← See Figures 3 and 4 →		
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	← 200 W →		
Continuous Device Dissipation at 100°C Case Temperature (See Note 3) 1	← 114 W →		
Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 4)	← 5 W →		
Unclamped Inductive Load Energy (See Note 5)	← 200 mJ →		
Operating Collector Junction Temperature Range	← -65°C to 200°C →		
Storage Temperature Range	← -65°C to 200°C →		
Terminal Temperature 1.6 mm from Case for 10 Seconds	← 250°C →		

- NOTES: 1. These values apply when the base-emitter diode is open-circuited.
2. This value applies for $t_w \leq 1$ ms, duty cycle $\leq 10\%$.
3. Derate linearly to 200°C case temperature at the rate of 1.14 W/°C or refer to Dissipation Derating Curve, Figure 5.
4. Derate linearly to 200°C free-air temperature at the rate of 28.6 mW/°C or refer to Dissipation Derating Curve, Figure 6.
5. This rating is based on the capability of the transistors to operate safely in the circuit of Figure 2. $L = 20$ mH, $R_{BB2} = 100 \Omega$, $V_{BB2} = 0$ V, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V. Energy $\approx I_C^2 L/2$.

*JEDEC registered data. This data sheet contains all applicable registered data in effect at the time of publication.

TYPES 2N6326, 2N6327, 2N6328

N-P-N SILICON POWER TRANSISTORS

*electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N6326		2N6327		2N6328		UNIT	
		MIN	MAX	MIN	MAX	MIN	MAX		
V _{(BR)CEO} Collector-Emitter Breakdown Voltage	I _C = 30 mA, I _B = 0, See Note 6	60		80		100		V	
I _{CEO} Collector Cutoff Current	V _{CE} = 30 V, I _B = 0		1					mA	
	V _{CE} = 40 V, I _B = 0				1				
	V _{CE} = 50 V, I _B = 0					1			
I _{CES} Collector Cutoff Current	V _{CE} = 60 V, V _{BE} = 0		0.5					mA	
	V _{CE} = 80 V, V _{BE} = 0			0.5					
	V _{CE} = 100 V, V _{BE} = 0					0.5			
	V _{CE} = 30 V, V _{BE} = 0, T _C = 150°C		5						
	V _{CE} = 40 V, V _{BE} = 0, T _C = 150°C				5				
	V _{CE} = 50 V, V _{BE} = 0, T _C = 150°C						5		
I _{EBO} Emitter Cutoff Current	V _{EB} = 5 V, I _C = 0,		0.5		0.5		0.5	mA	
h _{FE} Static Forward Current Transfer Ratio	V _{CE} = 4 V, I _C = 5 A		25		25		25		
	V _{CE} = 4 V, I _C = 15 A		12		12		12		
	V _{CE} = 4 V, I _C = 30 A		6	30	6	30	6		30
V _{BE} Base-Emitter Voltage	V _{CE} = 4 V, I _C = 15 A		2		2		2	V	
	V _{CE} = 4 V, I _C = 30 A		4		4		4		
V _{CE(sat)} Collector-Emitter Voltage	I _B = 2 A, I _C = 15 A		1.5		1.5		1.5	V	
	I _B = 7.5 A, I _C = 30 A		3		3		3		
h _{fe} Small-Signal Common-Emitter Forward Current Transfer Ratio	V _{CE} = 10 V, I _C = 1 A, f = 1 kHz		30		30		30		
h _{fe} Small-Signal Common-Emitter Forward Current Transfer Ratio	V _{CE} = 10 V, I _C = 1 A, f = 1 MHz		3		3		3		

NOTES: 6. These parameters must be measured using pulse techniques. $t_w = 300 \mu s$, duty cycle $\leq 2\%$.

7. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm from the device body.

*JEDEC registered data

switching characteristics at 25°C case temperature

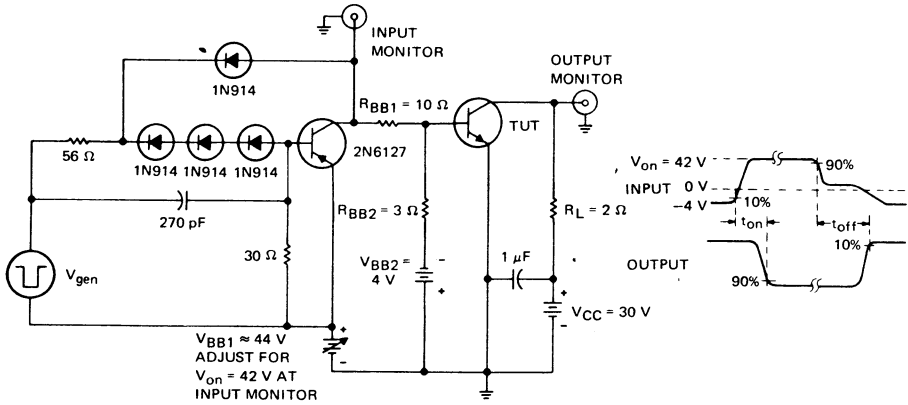
PARAMETER	TEST CONDITIONS [†]	TYP	UNIT
t _{on} Turn-On Time	I _C = 15 A, I _B (1) = 2 A, I _B (2) = -2 A,	0.6	μs
t _{off} Turn-Off Time	V _{BE(off)} = -4 V, R _L = 2 Ω, See Figure 1	0.9	

[†]Voltage and current values shown are nominal, exact values vary slightly with transistor parameters.

TEXAS INSTRUMENTS

TYPES 2N6326, 2N6327, 2N6328 N-P-N SILICON POWER TRANSISTORS

PARAMETER MEASUREMENT INFORMATION



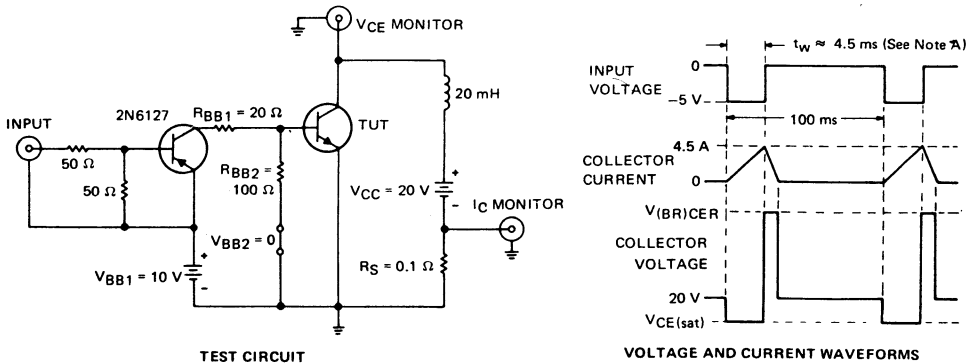
TEST CIRCUIT

VOLTAGE WAVEFORMS

- NOTES:
- A. V_{gen} is a -30-V pulse (from 0 V) into a $50\text{-}\Omega$ termination.
 - B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r \leq 15\text{ ns}$, $t_f \leq 15\text{ ns}$, $Z_{out} = 50\text{ }\Omega$, $t_w = 20\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 - C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 15\text{ ns}$, $R_{in} \geq 10\text{ M}\Omega$, $C_{in} \leq 11.5\text{ pF}$.
 - D. Resistors must be noninductive types.
 - E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1

INDUCTIVE LOAD SWITCHING



TEST CIRCUIT

VOLTAGE AND CURRENT WAVEFORMS

NOTE A: Input pulse width is increased until $I_{CM} = 4.5\text{ A}$.

FIGURE 2

TYPES 2N6326, 2N6327, 2N6328

N-P-N SILICON POWER TRANSISTORS

MAXIMUM SAFE OPERATING AREAS

MAXIMUM COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

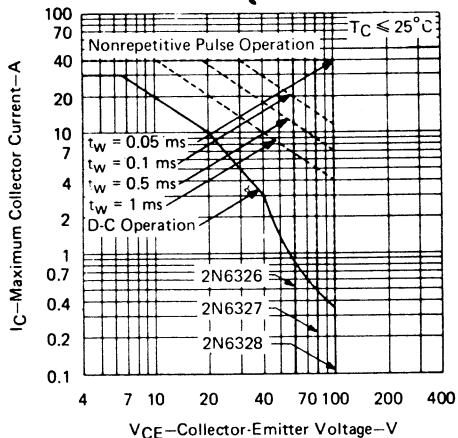


FIGURE 3

MAXIMUM COLLECTOR CURRENT
vs
UNCLAMPED INDUCTIVE LOAD

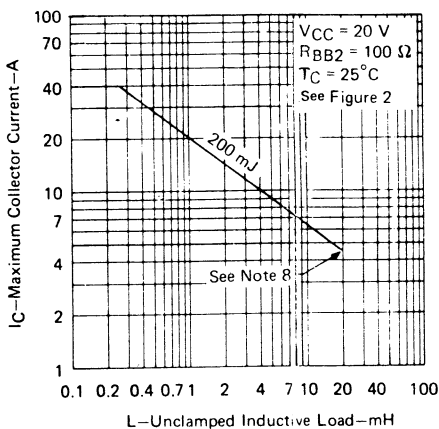


FIGURE 4

NOTE 8: Above this point the safe operating area has not been defined.

THERMAL INFORMATION

CASE TEMPERATURE
DISSIPATION DERATING CURVE

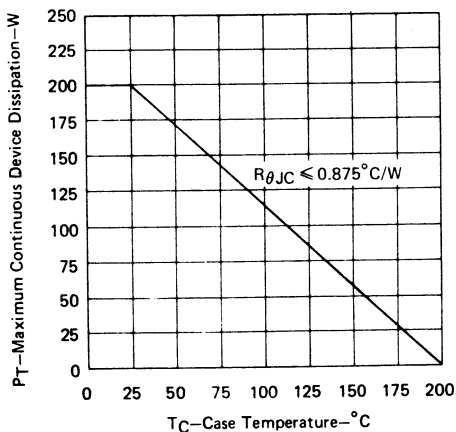


FIGURE 5

FREE-AIR TEMPERATURE
DISSIPATION DERATING CURVE

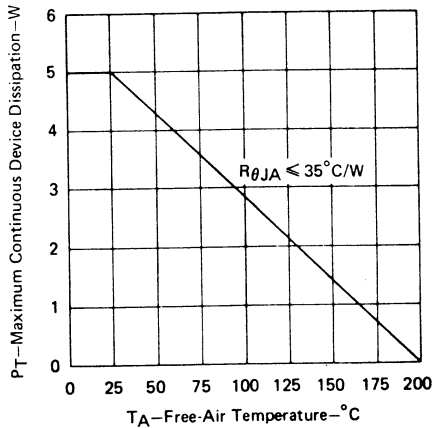


FIGURE 6

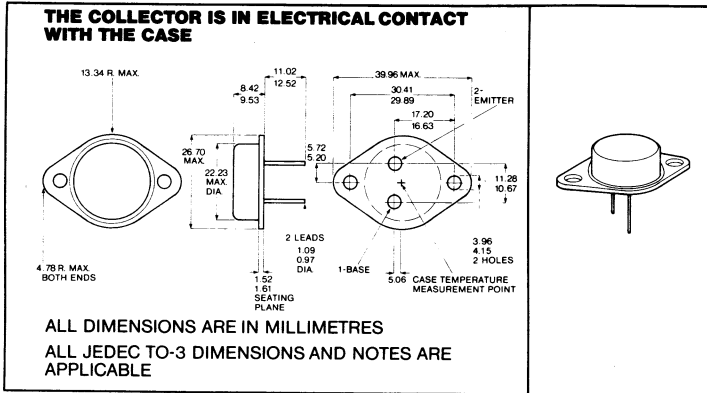
TEXAS INSTRUMENTS

TYPES 2N6329, 2N6330, 2N6331 P-N-P SILICON POWER TRANSISTORS

FOR POWER-AMPLIFIER AND HIGH-SPEED-SWITCHING APPLICATIONS
DESIGNED FOR COMPLEMENTARY USE WITH 2N6326, 2N6327, 2N6328

- 200 W at 25°C Case Temperature
- 30-A Rated Collector Current
- 200-mJ Reverse Energy Rating
- High SOA Capability, 20 V and 10 A

*mechanical data



*absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	2N6329	2N6330	2N6331
Collector-Base Voltage	-60 V	-80 V	-110 V
Collector-Emitter Voltage (See Note 1)	-60 V	-80 V	-100 V
Emitter-Base Voltage	-5 V	-5 V	-5 V
Continuous Collector Current	← -30 A →		
Peak Collector Current (See Note 2)	← -40 A →		
Continuous Base Current	← -10 A →		
Safe Operating Areas at (or below) 25°C Case Temperature	← See Figures 3 and 4 →		
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	← -200 W →		
Continuous Device Dissipation at 100°C Case Temperature (See Note 3)	← -114 W →		
Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 4)	← -5 W →		
Unclamped Inductive Load Energy (See Note 5)	← -200 mJ →		
Operating Collector Junction Temperature Range	← -65°C to 200°C →		
Storage Temperature Range	← -65°C to 200°C →		
Terminal Temperature 1.6mm from Case for 10 Seconds	← -250°C →		

- NOTES: 1. These value apply when the base-emitter diode is open-circuited.
 2. This value applies for $t_w \leq 1$ ms, duty cycle $\leq 10\%$.
 3. Derate linearly to 200°C case temperature at the rate of 1.14 W/°C or refer to Dissipation Derating Curve, Figure 5.
 4. Derate linearly to 200°C free-air temperature at the rate of 28.6 mW/°C or refer to Dissipation Derating Curve, Figure 6.
 5. This rating is based on the capability of the transistors to operate safely in the circuit of Figure 2. $L = 20$ mH, $R_{BB2} = 100 \Omega$, $V_{BB2} = 0$ V, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V. Energy $\approx I_C^2 L/2$.

*JEDEC registered data. This data sheet contains all applicable registered data in effect at the time of publication.

TYPES 2N6329, 2N6330, 2N6331

P-N-P SILICON POWER TRANSISTORS

*electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N6329		2N6330		2N6331		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
$V_{(BR)CEO}$ Collector-Emitter Breakdown Voltage	$I_C = -30$ mA, $I_B = 0$, See Note 6	-60		-80		-100		V
I_{CEO} Collector Cutoff Current	$V_{CE} = -30$ V, $I_B = 0$	-1						mA
	$V_{CE} = -40$ V, $I_B = 0$			-1				
	$V_{CE} = -50$ V, $I_B = 0$					-1		
I_{CES} Collector Cutoff Current	$V_{CE} = -60$ V, $V_{BE} = 0$		-0.5					mA
	$V_{CE} = -80$ V, $V_{BE} = 0$			-0.5				
	$V_{CE} = -100$ V, $V_{BE} = 0$					-0.5		
	$V_{CE} = -30$ V, $V_{BE} = 0$, $T_C = 150^\circ\text{C}$		-5					
	$V_{CE} = -40$ V, $V_{BE} = 0$, $T_C = 150^\circ\text{C}$			-5				
	$V_{CE} = -50$ V, $V_{BE} = 0$, $T_C = 150^\circ\text{C}$						-5	
I_{EBO} Emitter Cutoff Current	$V_{EB} = -5$ V, $I_C = 0$		-0.5		-0.5		-0.5	mA
h_{FE} Static Forward Current Transfer Ratio	$V_{CE} = -4$ V, $I_C = -5$ A	25		25		25		
	$V_{CE} = -4$ V, $I_C = -15$ A	12		12		12		
	$V_{CE} = -4$ V, $I_C = -30$ A	6	30	6	30	6	30	
V_{BE} Base-Emitter Voltage	$V_{CE} = -4$ V, $I_C = -15$ A		-2		-2		-2	V
	$V_{CE} = -4$ V, $I_C = -30$ A		-4		-4		-4	
$V_{CE(sat)}$ Collector-Emitter Voltage	$I_B = -2$ A, $I_C = -15$ A		-1.5		-1.5		-1.5	V
	$I_B = -7.5$ A, $I_C = -30$ A		-3		-3		-3	
h_{fe} Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = -10$ V, $I_C = -1$ A, $f = 1$ kHz	30		30		30		
h_{fe} Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = -10$ V, $I_C = -1$ A, $f = 1$ MHz	3		3		3		

NOTES: 6. These parameters must be measured using pulse techniques. $t_w = 300$ μ s; duty cycle $\leq 2\%$.

7. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 3.2 mm from the device body.

*JEDEC registered data

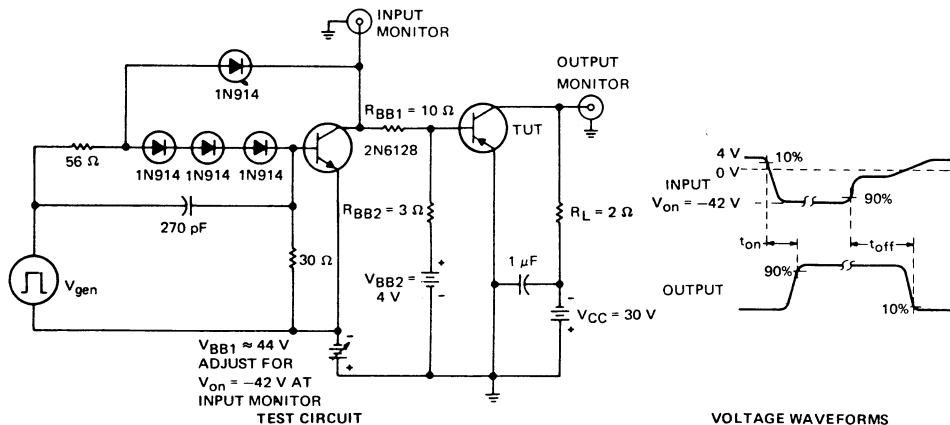
switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]	TYP	UNIT
t_{on} Turn-On Time	$I_C = -15$ A, $I_B(1) = -2$ A, $I_B(2) = 2$ A, $V_{BE(off)} = 4$ V, $R_L = 2$ Ω , See Figure 1	0.6	μ s
t_{off} Turn-Off Time		0.9	

[†]Voltage and current values shown are nominal, exact values vary slightly with transistor parameters.

TYPES 2N6329, 2N6330, 2N6331 P-N-P SILICON POWER TRANSISTORS

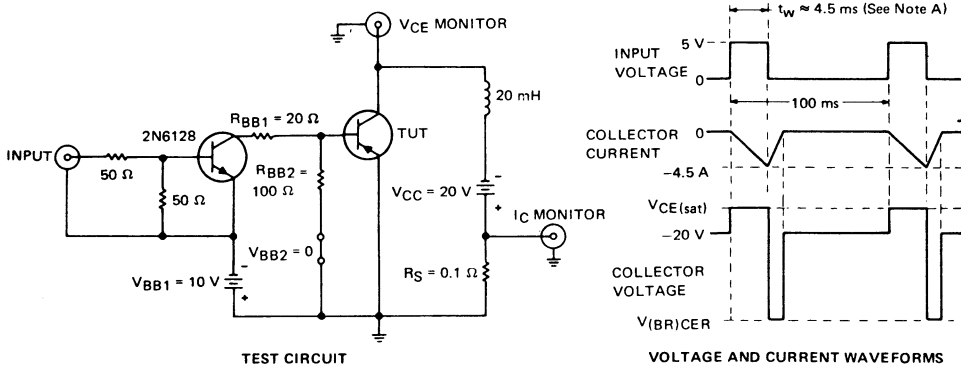
PARAMETER MEASUREMENT INFORMATION



- NOTES: A. V_{gen} is a 30-V pulse (from 0 V) into a 50- Ω termination.
 B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r \leq 15\text{ ns}$, $t_f \leq 15\text{ ns}$, $Z_{out} = 50\ \Omega$, $t_w = 20\ \mu\text{s}$, duty cycle $\leq 2\%$.
 C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 15\text{ ns}$, $R_{in} \geq 10\ \text{M}\Omega$, $C_{in} \leq 11.5\ \text{pF}$.
 D. Resistors must be noninductive types.
 E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1

INDUCTIVE LOAD SWITCHING



NOTE A: Input pulse width is increased until $I_{CM} = -4.5\text{ A}$.

FIGURE 2

TYPES 2N6329, 2N6330, 2N6331 P-N-P SILICON POWER TRANSISTORS

MAXIMUM SAFE OPERATING AREAS

MAXIMUM COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

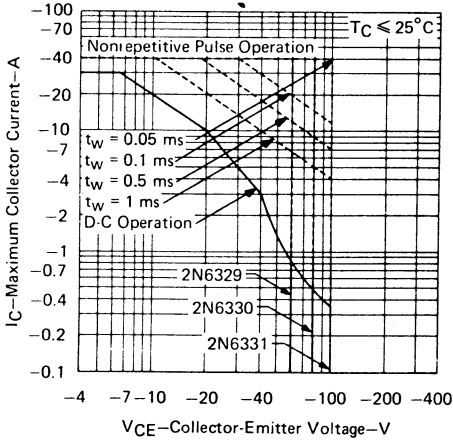


FIGURE 3

MAXIMUM COLLECTOR CURRENT
vs
UNCLAMPED INDUCTIVE LOAD

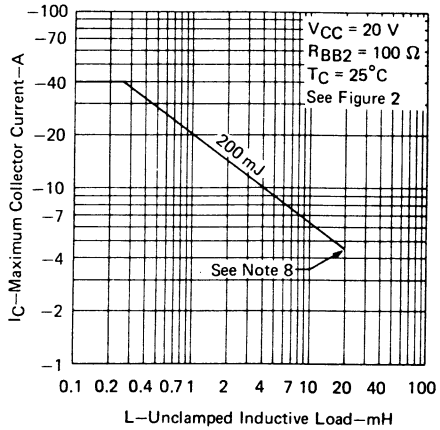


FIGURE 4

NOTE 8: Above this point the safe operating area has not been defined.

THERMAL INFORMATION

CASE TEMPERATURE
DISSIPATION DERATING CURVE

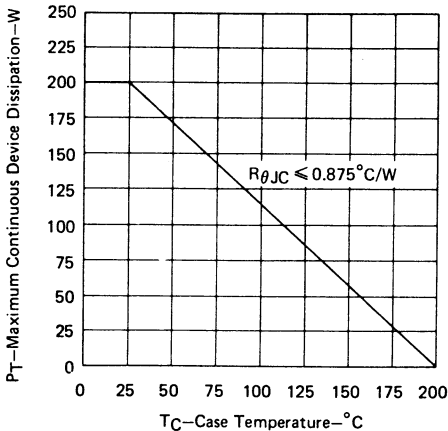


FIGURE 5

FREE-AIR TEMPERATURE
DISSIPATION DERATING CURVE

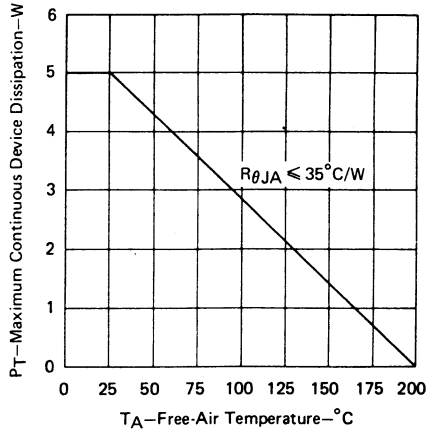


FIGURE 6

TEXAS INSTRUMENTS